

## Silicon NPN Power Transistors

2SC4467

## DESCRIPTION

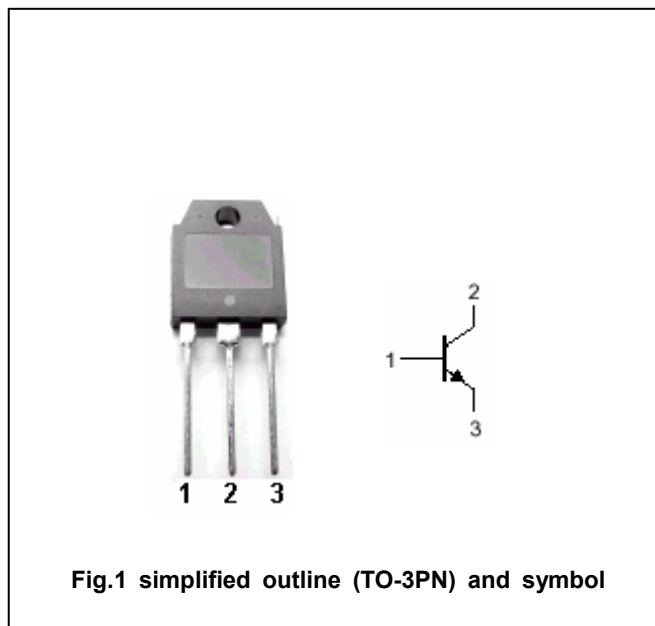
- With TO-3PN package
- Complement to type 2SA1694

## APPLICATIONS

- Audio and general purpose

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings( $T_a = \square$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	160	V
$V_{CEO}$	Collector-emitter voltage	Open base	120	V
$V_{EBO}$	Emitter-base voltage	Open collector	6	V
$I_C$	Collector current		8	A
$I_B$	Base current		3	A
$P_C$	Collector power dissipation	$T_C = 25 \square$	80	W
$T_j$	Junction temperature		150	$\square$
$T_{stg}$	Storage temperature		-55~150	$\square$

## Silicon NPN Power Transistors

## 2SC4467

## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =50mA ; I <sub>B</sub> =0	120			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =3A ; I <sub>B</sub> =0.3A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =160V; I <sub>E</sub> =0			10	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =6V; I <sub>C</sub> =0			10	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =3A ; V <sub>CE</sub> =4V	50		180	
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =10V, f=1MHz		200		pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =12V		20		MHz

## Switching times

t <sub>on</sub>	Turn-on time	I <sub>C</sub> =4A; R <sub>L</sub> =10Ω I <sub>B1</sub> =- I <sub>B2</sub> =0.4A V <sub>CC</sub> =40V		0.13		Ms
t <sub>s</sub>	Storage time			3.50		Ms
t <sub>f</sub>	Fall time			0.32		Ms

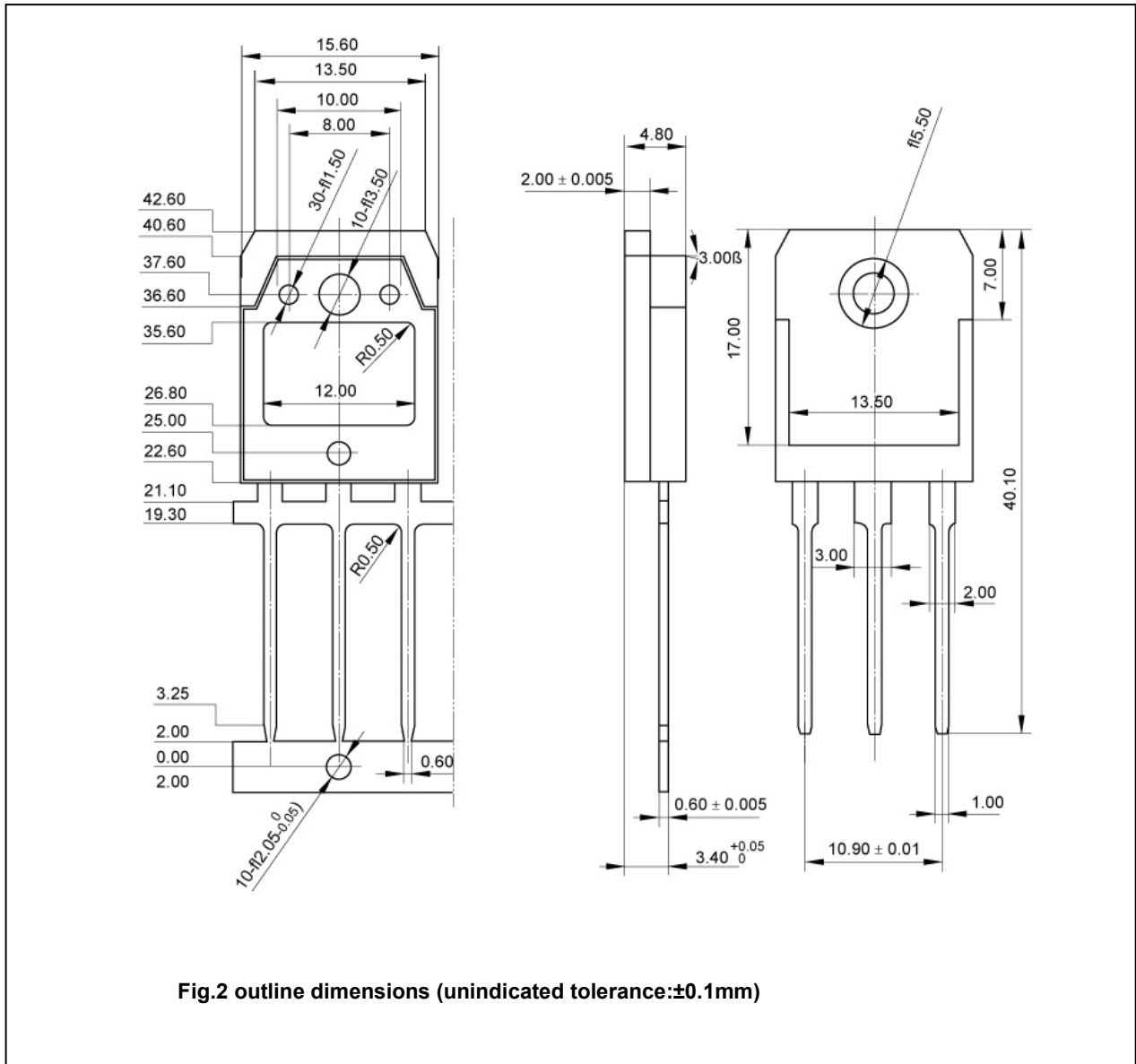
◆ h<sub>FE</sub> Classifications

O	P	Y
50-100	70-140	90-180

Silicon NPN Power Transistors

2SC4467

PACKAGE OUTLINE



Silicon NPN Power Transistors

2SC4467

